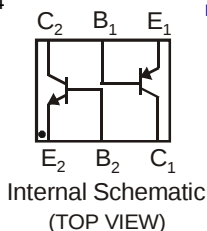


Features

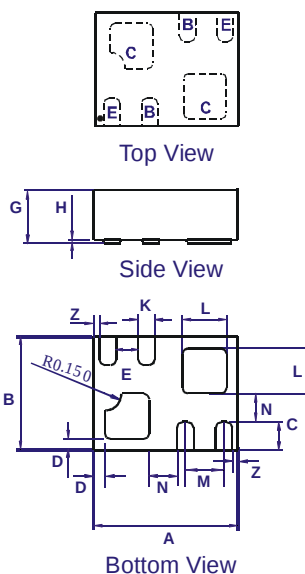
- Complementary Pair: One 3904 (NPN) and One 3906 (PNP)
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Lead Free by Design/RoHS Compliant (Note 1)**
- "Green" Device (Note 2)**

Mechanical Data

- Case: DFN1310H4-6
- Case Material: Molded Plastic. "Green Molding" Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish – NiPdAu over Copper leadframe (Lead Free Plating) Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 4
- Ordering Information: See Page 4



E₁, B₁, C₁ = PNP3906 Section
 E₂, B₂, C₂ = NPN3904 Section



DFN1310H4-6			
Dim	Min	Max	Typ
A	1.25	1.38	1.30
B	0.95	1.08	1.00
C	0.20	0.30	0.25
D*	-	-	0.10
E**	-	-	0.20
G	-	0.40	-
H	0	0.05	0.02
K*	0.10	0.20	0.15
L*	0.30	0.50	0.40
M**	-	-	0.35
N*	-	-	0.25
Z**	-	-	0.05

All Dimensions in mm

* Dimensions D, K, L, N Repeat 4X
 ** Dimensions E, M, Z Repeat 2X

Maximum Ratings, NPN 3904 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current – Continuous	I _C	200	mA
Power Dissipation (Notes 3, 4)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 3)	R _{θJA}	625	°C/W

Maximum Ratings, PNP 3906 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I _C	-200	mA
Power Dissipation (Notes 3, 4)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 3)	R _{θJA}	625	°C/W

- Notes:
- No purposefully added lead.
 - Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 - Device mounted on FR-4 PCB.
 - Maximum combined dissipation.

Electrical Characteristics, NPN 3904 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
Base Cutoff Current	I _{BL}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h _{FE}	40 70 100 60 30	— — 300 — —	—	I _C = 100μA, V _{CE} = 1.0V I _C = 1.0mA, V _{CE} = 1.0V I _C = 10mA, V _{CE} = 1.0V I _C = 50mA, V _{CE} = 1.0V I _C = 100mA, V _{CE} = 1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.20 0.30	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65 —	0.85 0.95	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.0	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = 20V, I _C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = 3.0V, I _C = 10mA,
Rise Time	t _r	—	35	ns	V _{BE(off)} = -0.5V, I _{B1} = 1.0mA
Storage Time	t _s	—	200	ns	V _{CC} = 3.0V, I _C = 10mA,
Fall Time	t _f	—	50	ns	I _{B1} = I _{B2} = 1.0mA

Electrical Characteristics, PNP 3906 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40	—	V	I _C = -10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40	—	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
Base Cutoff Current	I _{BL}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -3.0V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h _{FE}	60 80 100 60 30	— — 300 — —	—	I _C = -100μA, V _{CE} = -1.0V I _C = -1.0mA, V _{CE} = -1.0V I _C = -10mA, V _{CE} = -1.0V I _C = -50mA, V _{CE} = -1.0V I _C = -100mA, V _{CE} = -1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.25 -0.40	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65 —	-0.85 -0.95	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.5	pF	V _{CB} = -5.0V, f = 1.0MHz, I _E = 0
Current Gain-Bandwidth Product	f _T	250	—	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = -3.0V, I _C = -10mA,
Rise Time	t _r	—	35	ns	V _{BE(off)} = 0.5V, I _{B1} = -1.0mA
Storage Time	t _s	—	225	ns	V _{CC} = -3.0V, I _C = -10mA,
Fall Time	t _f	—	75	ns	I _{B1} = I _{B2} = -1.0mA

Notes: 5. Short duration test pulse used to minimize self-heating effect.

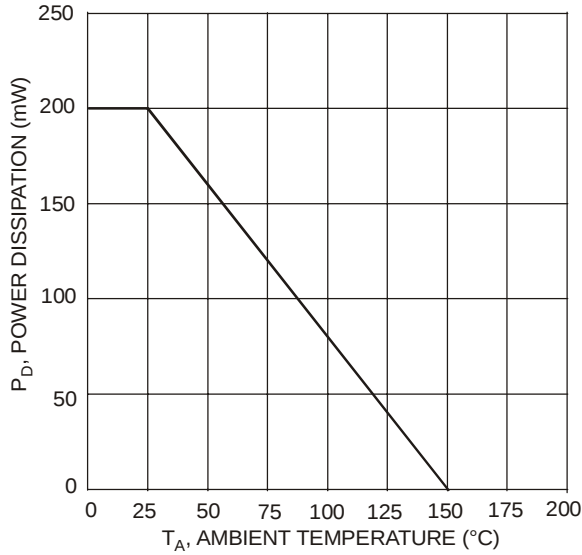


Fig. 1, Max Power Dissipation vs Ambient Temperature (Total Device) (Note 3)

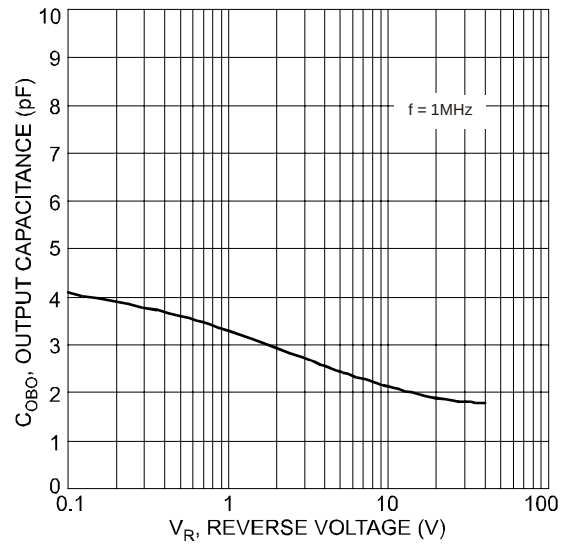


Fig. 2, Typical Output Capacitance Characteristics (NPN-3904)

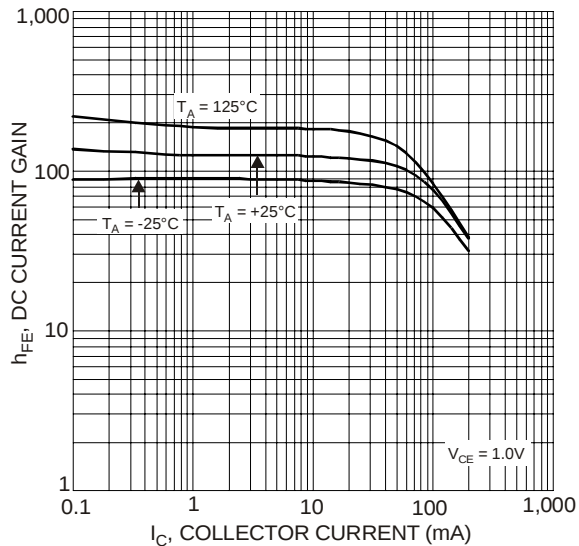


Fig. 3, Typical DC Current Gain vs Collector Current (NPN-3904)

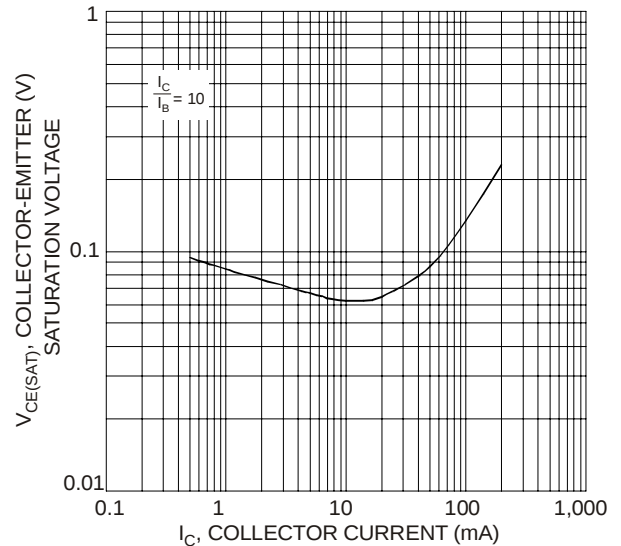


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current (NPN-3904)

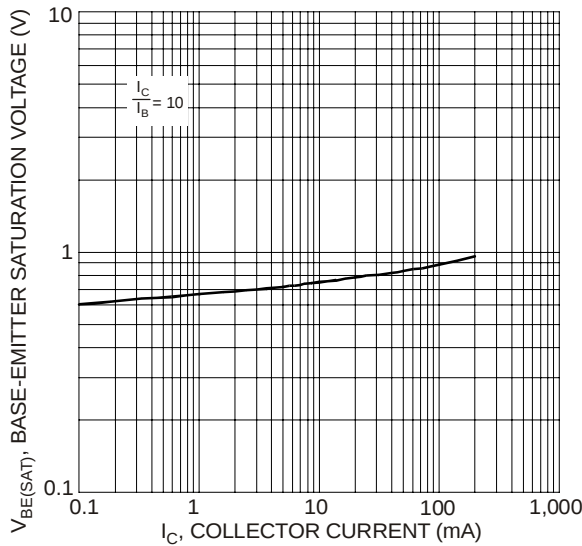


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current (NPN-3904)

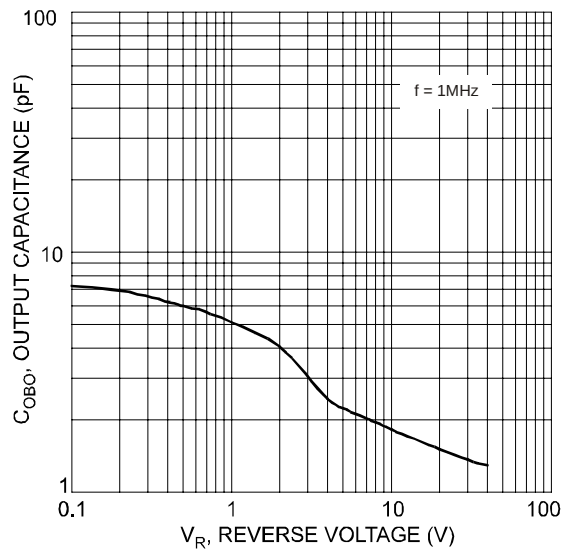


Fig. 6, Typical Output Capacitance Characteristics (PNP-3906)

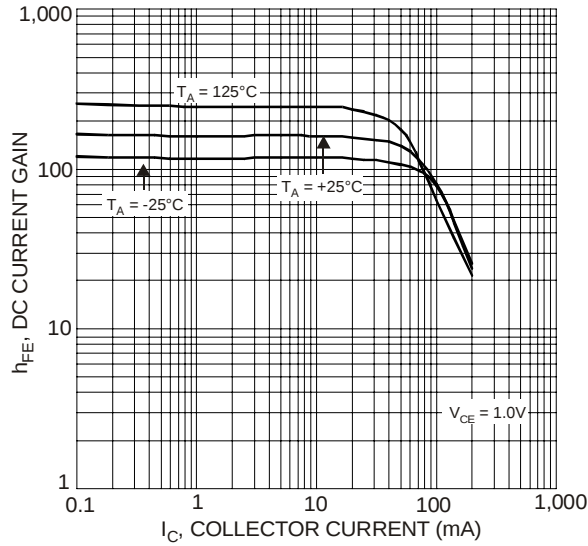


Fig. 7, Typical DC Current Gain vs Collector Current (PNP-3906)

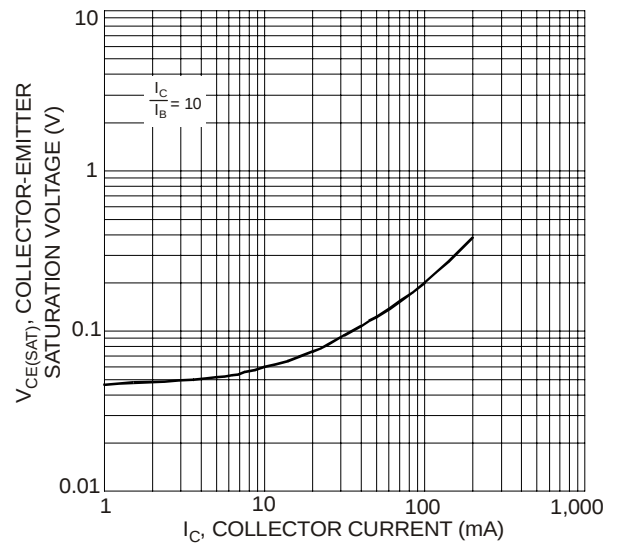


Fig. 8, Typical Collector-Emitter Saturation Voltage vs. Collector Current (PNP-3906)

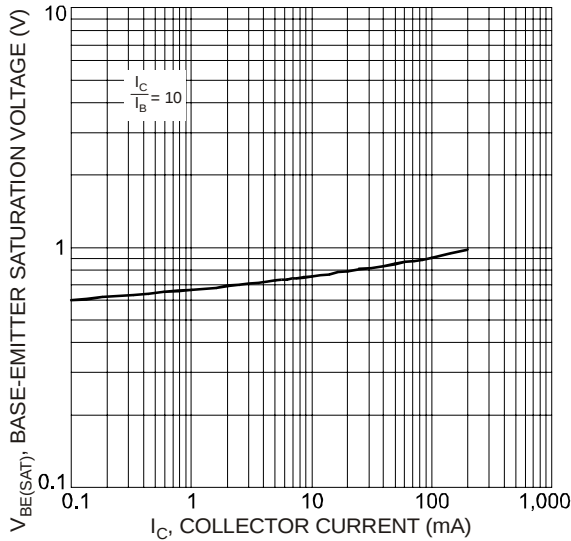


Fig. 9, Typical Base-Emitter Saturation Voltage vs. Collector Current (PNP-3906)

Ordering Information (Note 6)

Device	Packaging	Shipping
MMDT3946LP4-7	DFN1310H4-6	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



46= Product Type Marking Code

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9